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- (54) **ORGANIC SEMICONDUCTOR LASER**
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- (\*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

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This patent is subject to a terminal disclaimer.

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- (22) Filed: **Aug. 25, 2000**

**Related U.S. Application Data**

- (63) Continuation of application No. 08/859,468, filed on May 19, 1997, now Pat. No. 6,111,902.
- (60) Provisional application No. 60/046,061, filed on May 9, 1997.
- (51) **Int. Cl.<sup>7</sup>** ..... **H01S 3/16**
- (52) **U.S. Cl.** ..... **372/39; 53/70**
- (58) **Field of Search** ..... **372/39, 53, 70**

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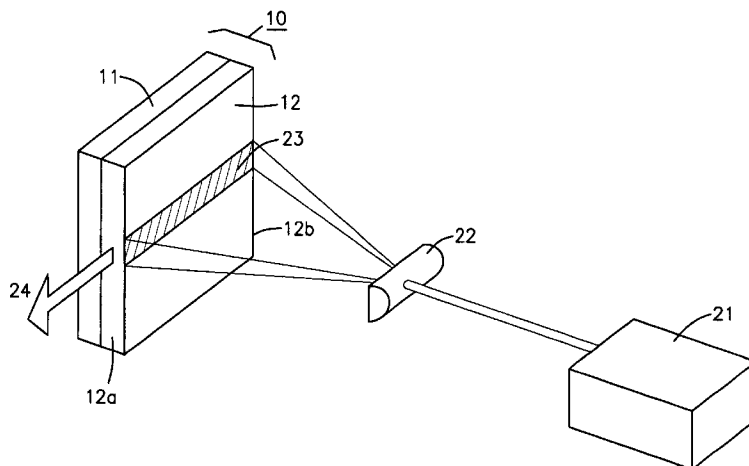
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(57) **ABSTRACT**

An optically-pumped laser having a small-molecule thin organic film of DCM doped Alq<sub>3</sub>. Carrier transport properties of the small-molecule organic materials, combined with a low lasing threshold provide a new generation of diode lasers employing organic thin films. An electrically-pumped variant is also described.

**60 Claims, 6 Drawing Sheets**



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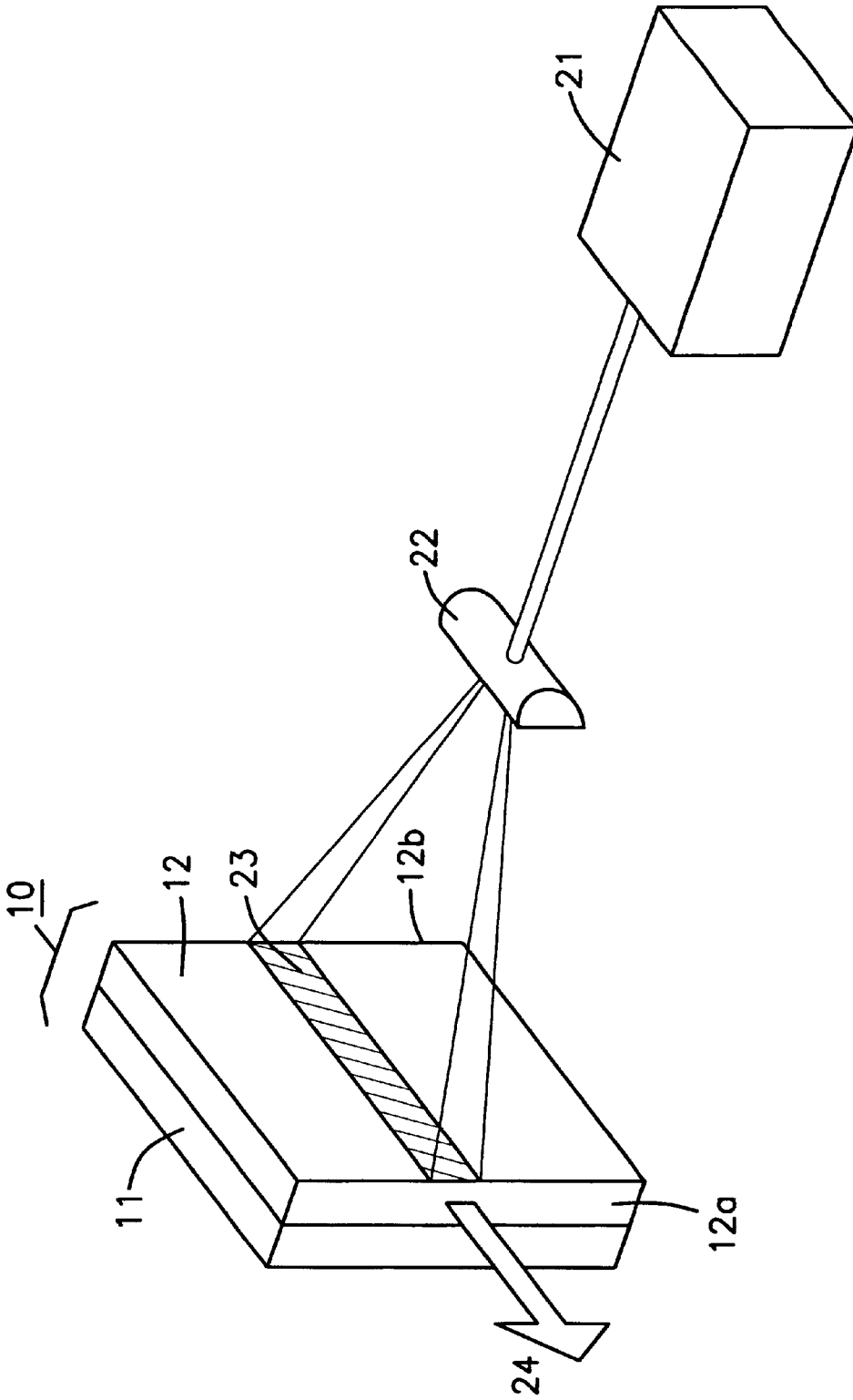


FIG. 1

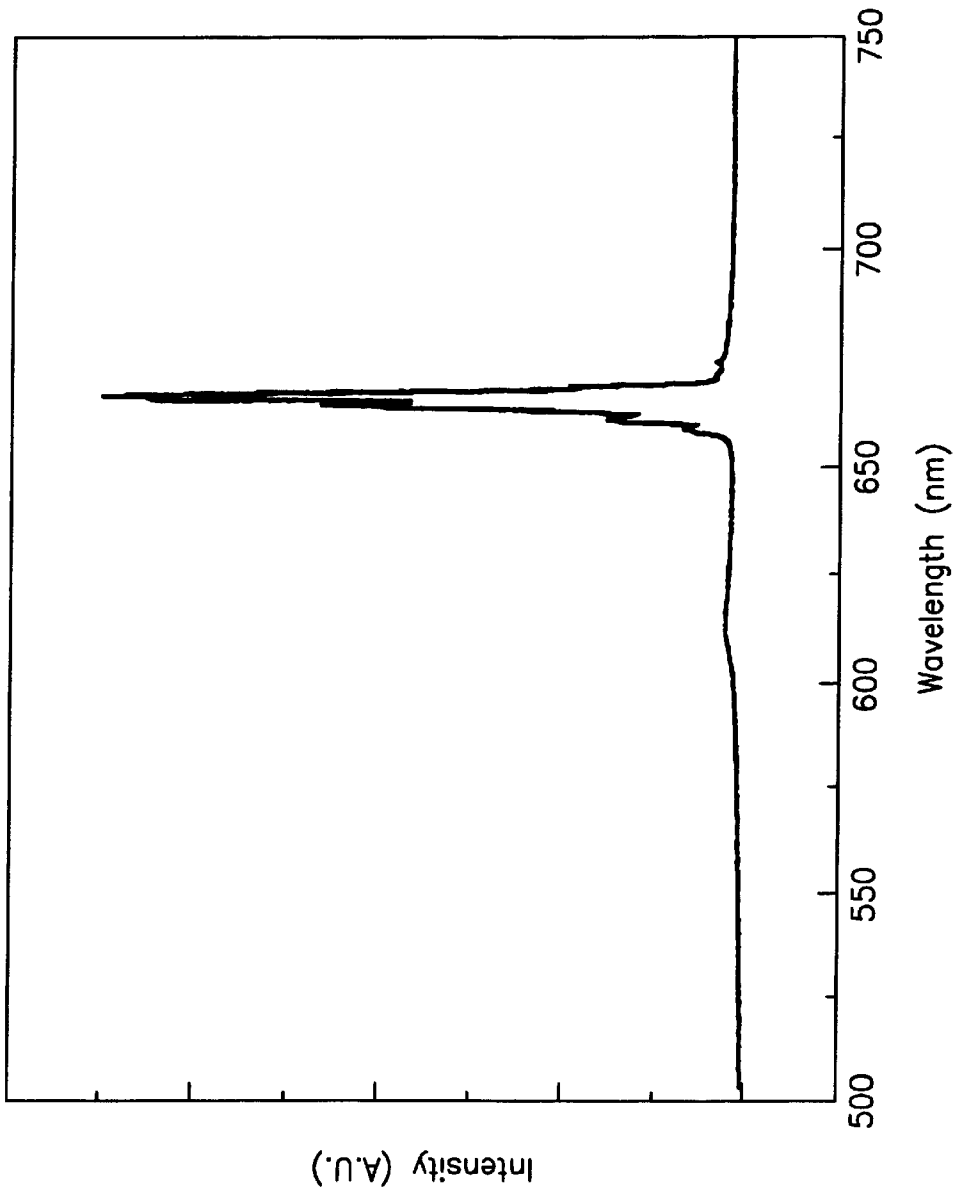


FIG. 2

FIG. 3A

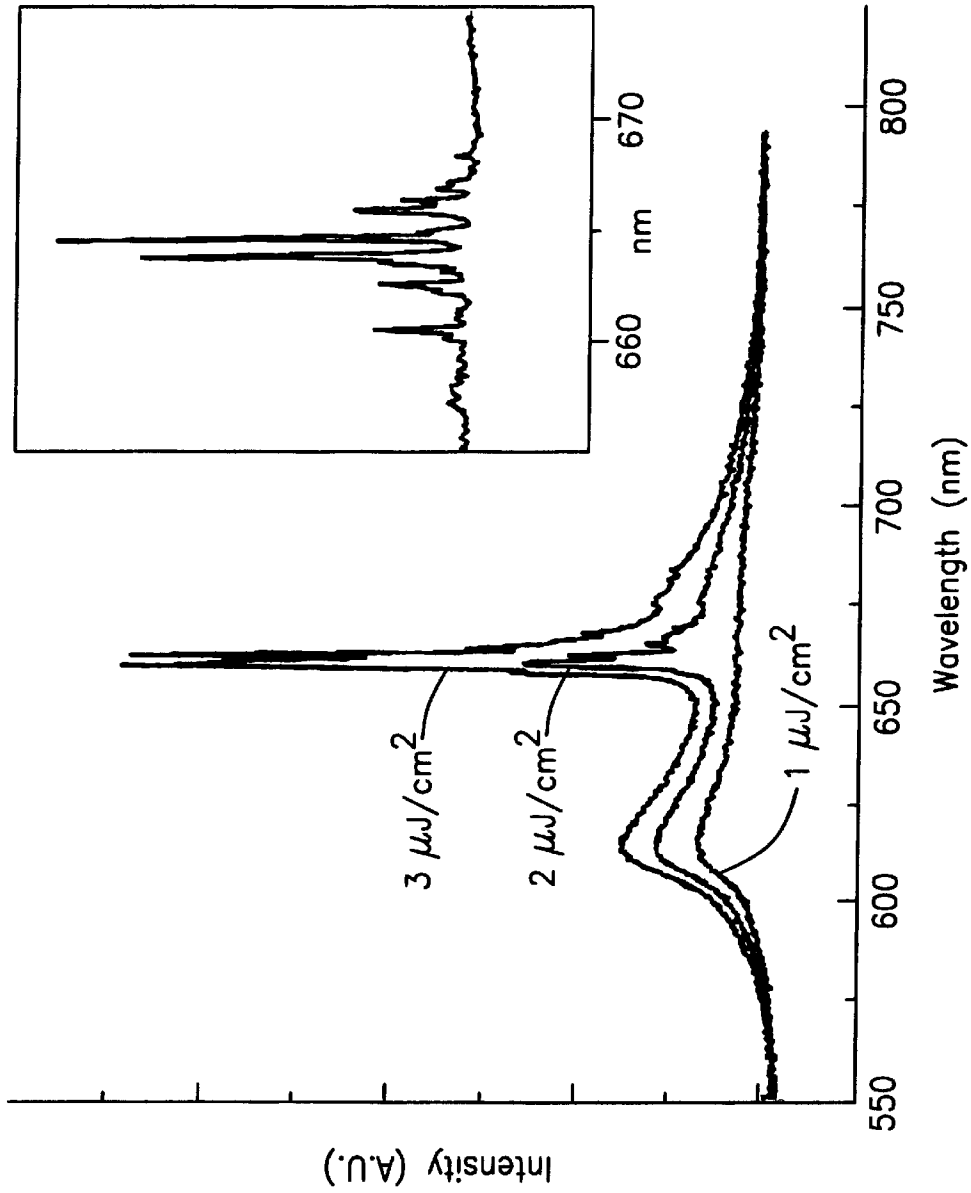


FIG. 3

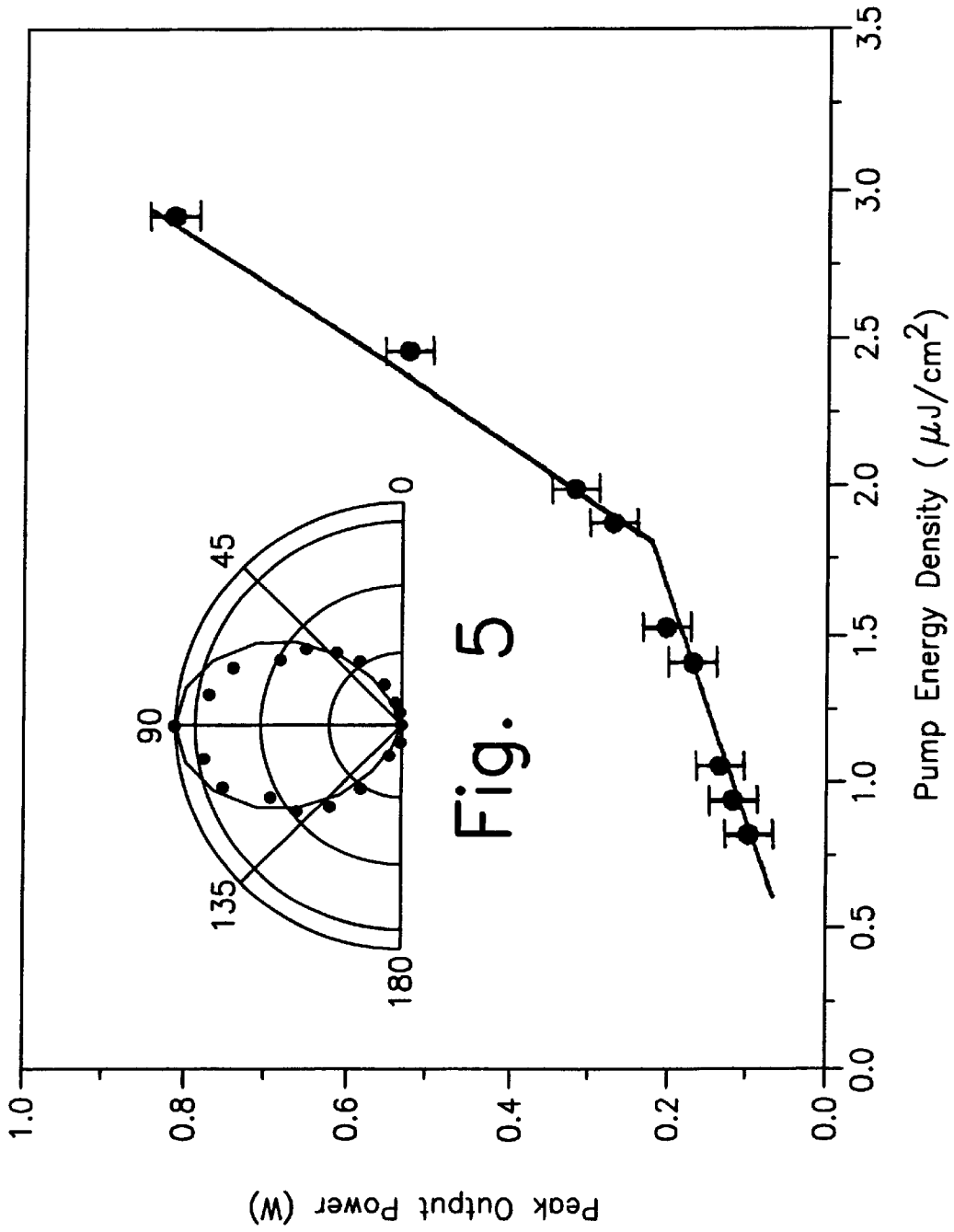


Fig. 5

FIG. 4

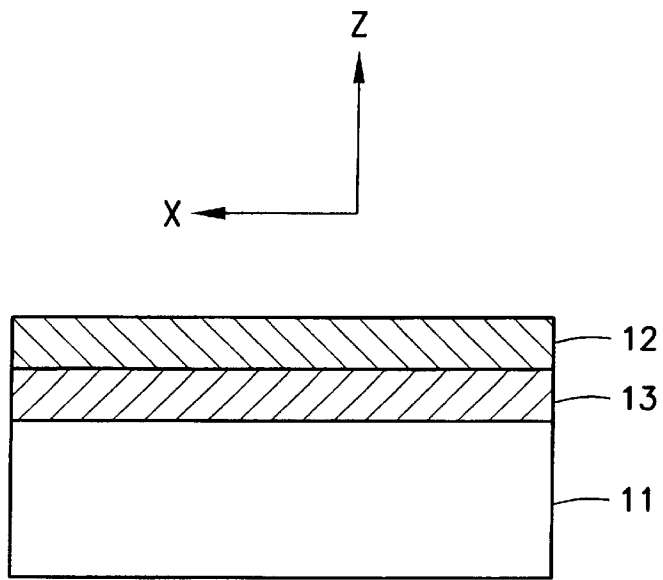


FIG. 6A

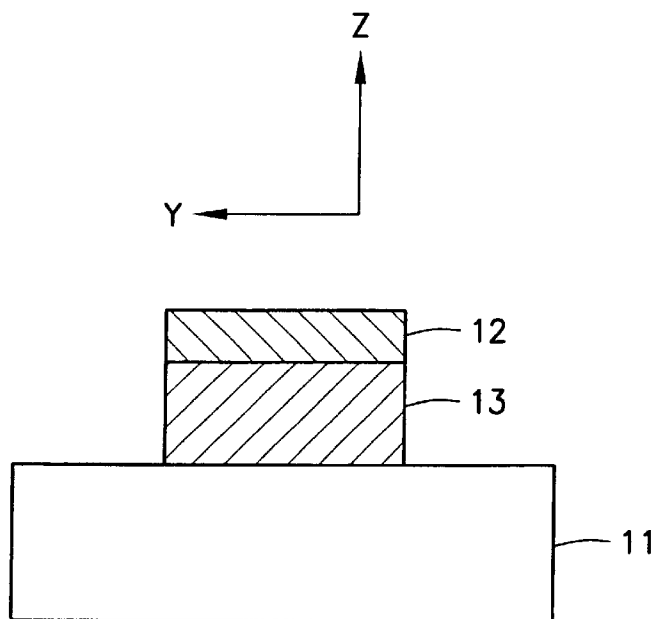


FIG. 6B

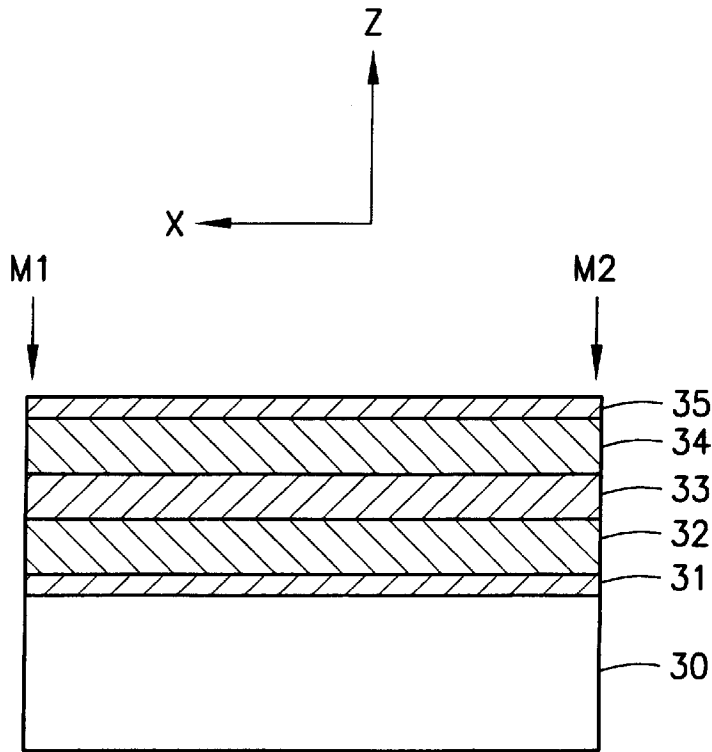


FIG. 7A

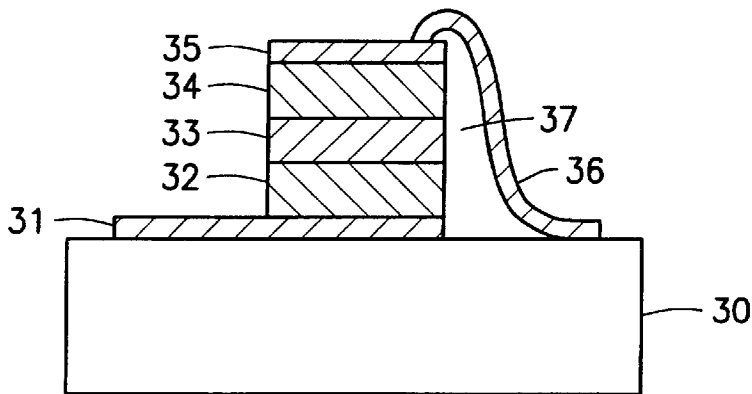


FIG. 7B



## ORGANIC SEMICONDUCTOR LASER

## RELATED APPLICATIONS

This application is a continuation of Ser. No. 08/859,468 filed May 19, 1997 U.S. Pat. No. 6,111,902 claims the benefit, under 35 U.S.C. §119(e)(2), of a U.S. Provisional Application 60/046,061 filed on May 9, 1997 and entitled ORGANIC SEMICONDUCTOR LASER.

## GOVERNMENT RIGHTS

This invention was made with Government support under Contract No. F49620-96-1-0277 awarded by AFOSR and Contract No. DMR94-00362 awarded by NSF/MRSEC. The government has certain rights in this invention.

## FIELD OF THE INVENTION

The present invention relates to the field of light emitting devices, in particular, to organic semiconductor lasers.

## BACKGROUND INFORMATION

Several recent publications have reported either superluminescence or amplified spontaneous emission in polymeric organic light emitters such as conjugated polymers. (N. Tessier et al., *Nature* 382, 695 (1996); F. Hide et al., *Science* 273, 1833 (1996)). The materials used in those emitters were spin-coated from a solution of the polymer or its chemical precursors. Optically pumped, stimulated emission from organic laser dyes, introduced into inert, spin-coated polymers or gels has been described in the literature. (R. E. Hermes, et al., *Appl. Phys. Lett.* 63, 877 (1993); M. N. Weiss et al., *Appl. Phys. Lett.* 69, 3653 (1996); H. Kogelnik et al., *Appl. Phys. Lett.* 18, 152 (1971); M. Canva et al., *Appl. Opt.*, 34, 428 (1995)).

Recent work has demonstrated gain-narrowed photoluminescence spectra with full widths at half maxima (FWHM) of 40–60 Å in response to a short pulse laser excitation, typically 1 μJ in a 10 ns pulse. (Materials Research Society 1997 Spring Meeting, Abstracts H1.1, H1.6, H2.1, H2.2, H2.3.) Such work is potentially applicable to electrically pumped organic solid state lasers “plastic lasers”). If realized, such devices could offer low cost and ease of integration of laser sources onto either conventional semiconductor circuitry or lightweight plastic substrates.

Spun-on polymeric materials, however, do not exhibit particularly good thickness uniformity, ability to achieve extremely high materials purity, and ease of integration with other conventional semiconductor fabrication processes.

In the field of organic light emitting devices (OLEDs) for flat panel display applications, small molecule OLEDs currently offer better operating lifetimes by an order of magnitude over their spin-coated, polymeric analogs. (L. J. Rothberg et al., “Status of and Prospects for Organic Electroluminescence”, *J. Mater. Res.* 1996, 11:3174; N. C. Greenham et al., “Semiconductor Physics of Conjugated Polymers”, *Solid State Physics* 1995, 49:1.)

However, there has been no known demonstration of laser action in a vacuum-deposited organic thin film structure. Furthermore, there is considerable skepticism about the realization of small-molecule organic lasers because of quenching processes which can occur in such materials. Such quenching processes are observed at high carrier densities and lead to decreased photoluminescence quantum efficiency. For example, bimolecular reactions in Alq<sub>3</sub> films have been found to cause the quantum efficiency of photoluminescence to begin to decrease at incident intensities

above 10<sup>14</sup> photons/cm<sup>2</sup>. (D. Y. Zang et al., *Appl. Phys. Lett.* 60 (2), 189, 1992.)

## SUMMARY OF THE INVENTION

The present invention is directed to a small-molecule, organic thin film laser with very low threshold lasing. Both optically and electrically pumped embodiments are disclosed.

In contrast to spun-on polymeric materials, vacuum-deposition of small molecular weight organic materials offers the advantages of excellent thickness uniformity, extremely high materials purity, and ease of integration with other conventional semiconductor fabrication processes.

In an exemplary embodiment of the present invention, very low threshold, optically-pumped lasing is achieved in a vacuum-deposited, organic thin film comprising a layer of tris(8-hydroxyquinoline) aluminum (Alq<sub>3</sub>) doped with DCM laser dye. A very low lasing threshold is achieved at a pump energy density of 1.5 μJ/cm<sup>2</sup> with a 500 psec excitation pulse. Above the threshold, several extremely narrow (i.e., less than 1 Å FWHM), linearly polarized Fabry-Perot modes appear in the output spectrum. The peak output power above the threshold exceeds 30 W from a 3×10<sup>-7</sup> cm<sup>2</sup> output facet, corresponding to a peak power of approximately 10<sup>8</sup> W/cm<sup>2</sup>.

Bright red laser emission is clearly visible from the edge of the device. The output laser beam includes several transverse modes which diverge in a direction orthogonal to the surface of the device of the present invention. The emission is strongly linearly polarized, as one would expect for laser emission. No appreciable degradation of laser material occurs after several hours of pulsed operation in a dry nitrogen atmosphere.

The present invention provides a laser device with a small-molecule, vacuum-depositable organic thin film which exhibits a low lasing threshold (1.5 μJ/cm<sup>2</sup>), high efficiency, narrow line width (less than 1 Å) and high peak power (30 W). The pump threshold corresponds to a current density of 10–50 A/cm<sup>2</sup> for an electrically pumped laser using such materials.

The ease of processing, low threshold and other characteristics of vacuum-deposited materials opens the door to an entirely new generation of optically and electrically-pumped solid-state lasers using vacuum-deposited organic semiconductors.

The laser of the present invention can be used in a wide variety of applications, including telecommunications, printing, optical downconversion, semiconductor circuit etching, thermal processing (e.g., marking, soldering and welding), spectroscopy, vehicular control and navigation, measurement devices, optical memory devices, displays, scanners, pointers, games and entertainment systems and sensors.

## BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 shows an arrangement including a laser device in accordance with the present invention.

FIG. 2 shows the spectrum of the edge emission from a device in accordance with the present invention.

FIGS. 3 and 3A show spectra of the edge emission from a device in accordance with the present invention at different excitation levels near the lasing threshold.

FIG. 4 shows, for a device in accordance with the present invention, the dependence of the output emission intensity on the input pump energy density near the lasing threshold of the device.

FIG. 5 shows the polarization of the emission of a device in accordance with the present invention, as a function of the angle between a plane orthogonal to the film surface and the plane of a polarizer.

FIGS. 6A and 6B show further embodiments of optically-pumped laser devices in accordance with the present invention.

FIGS. 7A and 7B show embodiments of electrically-pumped laser devices in accordance with the present invention.

#### DETAILED DESCRIPTION

FIG. 1 shows an optically-pumped laser arrangement including an organic film laser 10 in accordance with the present invention. The device of FIG. 1 comprises a small-molecule vacuum-depositable, organic film 12 including a layer of tris-(8-hydroxyquinoline) aluminum (Alq<sub>3</sub>) doped with DCM laser dye. Such a dye is available from Exciton Inc. of Dayton, Ohio.

The device 10 of FIG. 1 exhibits a very low lasing threshold at a pump energy density of 1.5 μJ/cm<sup>2</sup> with a 500 psec excitation pulse. Above the lasing threshold, several extremely narrow, i.e., less than 1 Å FWHM, linearly polarized Fabry-Perot modes appear in the output spectrum between 660 nm and 670 nm. The peak output power above the threshold is at least 30 W from a 3×10<sup>-7</sup> cm<sup>2</sup> output facet.

Doping Alq<sub>3</sub> with a red dye such as DCM provides an excellent laser material because the red emission (and optical gain) generated is far away from the absorption edge of the Alq<sub>3</sub> host material (at 450 nm). Doping also allows reduction of the density of the optically active DCM molecules (thereby reducing the effective density of states), which lowers the threshold and increases the efficiency of the laser.

The concentration of the dopant in the thin film 12 can typically be selected to be less than 10%, by mass, but can be as low as 0.01%. The optimal concentration of DCM, i.e., that concentration which will yield the lowest lasing threshold, is that concentration which will provide sufficient optical gain to overcome the optical losses of the device 10. A low concentration, however, prevents clustering, thereby reducing non-radiative losses. In an exemplary embodiment, a concentration of 1.5% was found to be optimal for a 3 mm long device.

DCM is a good active dopant because it can be vacuum deposited along with the Alq<sub>3</sub> and because it has a very high absorbance in the green spectral range, thereby providing for efficient energy transfer from the Alq<sub>3</sub> to the DCM molecules.

Other combinations of host and dopant materials can be used to form the film 12. For example, ALX can be used instead of Alq<sub>3</sub> as the host material and coumarin (C6) can be used instead of DCM as the dopant. Any combination of host and dopant materials which allows for good energy transfer between the host and dopant and in which the host is transparent, or nearly transparent, in the spectral range of the dopant can be used in the optically-pumped embodiment of the present invention.

Although the laser device 10 described thus far is an optically-pumped device, the Alq<sub>3</sub>/DCM film 12 used in the device 10 has the advantage of being conducive to electrical pumping because Alq<sub>3</sub> is an efficient electron transporting material.

The laser device of the present invention can be grown on any substrate to which the organic film will adhere and

which has a lower index of refraction (n) than the organic film material. Acceptable substrates include some plastics, glass and silicon coated with SiO<sub>2</sub>.

In an exemplary embodiment, the device 10 is grown on a glass slide 11 by high vacuum (5×10<sup>-7</sup> Torr) co-evaporation of Alq<sub>3</sub> and DCM in a molecular ratio of approximately 50:1. This ratio is controlled by independently varying the evaporation rate of each constituent molecule. A 3000 Å thick film of Alq<sub>3</sub>/DCM, having an optical index of refraction (n) of 1.7, forms a slab optical waveguide with glass (n=1.4) as a cladding layer on one side, and air (n=1) on the other. This slab optical waveguide in conjunction with reflective facets 12a and 12b of the deposited organic film layer 12 form an optical resonator. Lateral confinement of the optical mode is achieved by gain-guiding induced by the optical pump beam. The thickness of the organic film is selected to be large enough to provide waveguiding within the organic film. Also, whereas a thickness of 3000 Å is optimal for single-mode propagation within the Alq<sub>3</sub>/DCM film, higher-order modes can be supported by correspondingly thicker films.

The formation of optically smooth, sharp facets 12a and 12b at opposing edges of the device 10 is a natural advantage of vacuum-deposited films. The shape of the facets 12a and 12b will follow the shape of the corresponding facets of the underlying substrate 11. As such, it is important that the facets of the substrate 11 be smooth and parallel to each other. The above-described process provides a technique for fabricating optical cavities without additional processing. By such means, facet reflectivities of 7% are obtained, which is sufficient to provide the necessary optical feedback. Furthermore, as is known, optical feedback can be achieved with other structures as well, such as by an optical grating placed underneath the optically pumped region of the organic film, thereby forming a distributed feedback structure, if the grating blaze separation is  $m\lambda/2n_o$ , where  $m=1, 2, \dots$

In the alternative, the film 12 can be deposited on the substrate 11 and the combination then cleaved to form smooth, sharp facets.

The device 10 of the present invention can be optically pumped using any light source emitting light of sufficient intensity which can be absorbed by the host material molecular species. In the exemplary embodiment of FIG. 1, the device 10 is optically pumped using a nitrogen laser 21 which generates 500 psec pulses with a wavelength of 337 nm at a 50 Hz repetition rate. As shown in FIG. 1, the pump beam is focused, such as by a cylindrical lens 22, into a 100 μm wide stripe 23 on the film surface oriented orthogonal to the facets 12a and 12b of the device. The refractive index of the illuminated portion of the organic film 12 is higher than that of the non-illuminated portion, thereby providing confinement of the optical mode in the vertical direction. This is the gain-guiding effect referred to above.

A laser beam 24 is emitted from a facet 12a and/or 12b of the device 10. A typical length for a device in accordance with the present invention is 25 mm, although devices of shorter length, e.g., 0.5 mm, can be implemented.

Although the reflectivity of the edge facets is small, this is compensated for by the comparatively large cavity length, thereby reducing effective optical losses to approximately 1 cm<sup>-1</sup> (neglecting waveguide losses).

Because the material is essentially transparent to DCM red emission, it is not necessary to pump the whole length of the optical cavity to achieve lasing action. Optical gain in the Alq<sub>3</sub>/DCM film is so high that lasing can be achieved, for

instance, by pumping the film of a 25 mm long device over only 1 mm of the device's length. However, pumping the device over a larger portion of its length, e.g. 20 mm, allows for lower threshold powers.

The edge emission spectrum of the device of the present invention can be analyzed by a spectrograph and a CCD camera. FIG. 2 shows the spectrum of the edge emission from a device in accordance with the present invention. The spectrum of FIG. 2 was exhibited at a pump energy density of  $15 \mu\text{J}/\text{cm}^2$ , which is approximately 10 times the lasing threshold of the device.

FIG. 3 shows how the emission spectrum of the device of FIG. 1 varies as the pump energy density varies near the  $1.5 \mu\text{J}/\text{cm}^2$  lasing threshold of the device. Below the threshold, the edge emission spectrum is dominated by a broad peak centered at a wavelength of 620 nm. This peak is characteristic of spontaneous emission from DCM. No emission from the  $\text{Alq}_3$  is seen under any of the pump intensities, thus indicating complete energy transfer between the  $\text{Alq}_3$  host and the DCM. Laser emission appears as a sharp peak on the long wavelength side of the photoluminescence spectrum at pump energy densities as low as  $1.5 \mu\text{J}/\text{cm}^2$ . Edge emission spectra are completely dominated by laser peaks at high excitation levels (i.e., above  $5 \mu\text{J}/\text{cm}^2$ , as in the spectrum shown in FIG. 2).

FIG. 3A shows a high resolution edge emission spectrum of the device of FIG. 1 at a pump level of  $1.7 \mu\text{J}/\text{cm}^2$ . The spectrum of FIG. 3A reveals a set of longitudinal lasing modes. A mode competition process is clearly indicated by the irregular spacing of these modes. The spectral width of the peaks is limited by the resolution of the spectrograph. (The separate longitudinal modes of a 25 mm long optical cavity are expected to have a wavelength spacing of  $0.04 \text{ \AA}$ , which is well below the  $1 \text{ \AA}$  resolution limit of a typical spectrograph.) FIG. 4 shows the dependence of the device's peak output power to the pump energy density. From this relationship, the lasing threshold can be clearly discerned. Each line segment in the graph of FIG. 4 is a linear fit to empirically measured points. The slopes of the two line segments emphasize a change in differential quantum efficiency, from 0.2%, below the lasing threshold, to 10% above the lasing threshold. It is to be noted, however, that measured differential quantum efficiencies represent a considerable underestimation since the lasing region in an optically pumped gain-guided device is only a small fraction of the material which is being pumped. Hence, most of the pump power is lost in non-lasing regions. The differential quantum efficiency decreases to 7% at excitation levels above  $10 \mu\text{J}/\text{cm}^2$  (not shown), corresponding to peak output powers exceeding 4 W.

FIG. 5 shows the intensity of laser emission passing through a polarizer as a function of angle between the plane orthogonal to the film surface and the plane of the polarizer. The emission is strongly linearly polarized, as is expected for laser emission. The degree of polarization measured is 15 dB, although it should be noted that this result is limited by the measurement arrangement. The solid line, which is a fit of the empirically measured points, follows  $\sin^2(\alpha)$ , where  $\alpha$  is the polarizer angle.

With the exemplary embodiment of FIG. 1, bright red laser emission is clearly visible from the edge of the device. Diffraction of the output beam is faintly observed. The output laser beam includes several transverse modes which diverge in the direction orthogonal to the device surface. The peak intensity of the red laser emission at the output facets is  $10^8 \text{ W}/\text{cm}^2$  (corresponding to a measured peak power exceeding 30 W) at a pump level of  $200 \mu\text{J}/\text{cm}^2$ .

All experiments and empirical measurements described above were conducted under a dry nitrogen atmosphere. No degradation of the  $\text{Alq}_3/\text{DCM}$  film of the device of the present invention was observed after several hours of operation (which corresponds to at least  $10^6$  laser pulses). This indicates that the  $\text{Alq}_3/\text{DCM}$  thin film enjoys a high degree of photochemical stability and that it is well suited for use in electrically pumped organic lasers.

Furthermore, the very low lasing threshold of the device of the present invention is also a significant advantage over known devices. Assuming a carrier lifetime of 10 ns for  $\text{Alq}_3$  and DCM, a lasing threshold energy density of  $1.5 \mu\text{J}/\text{cm}^2$  implies a  $10\text{--}50 \text{ A}/\text{cm}^2$  threshold current density for pulsed electrical injection, assuming that only 25% of electrically injected carriers form singlet excitations. The lasing threshold can be reduced even further by controlling the doping concentration and increasing the facet reflectivities, both of which are factors affecting the efficiency of the laser device.

The device of the present invention also overcomes the problems related to quenching processes in small-molecule organic materials. Such quenching processes are observed at high carrier densities and lead to decreased photoluminescence quantum efficiency. It has been found that, due to bimolecular reactions, the quantum efficiency of photoluminescence of  $\text{Alq}_3$  films begins to decrease at incident intensities above  $10^{14}$  photons/ $\text{cm}^2$ . The device of the present invention, however, has a lasing threshold which is at pump intensities of only approximately  $10^{12}$  photons/ $\text{cm}^2$ , leaving a substantial margin for increasing pump intensities without encountering a decrease in efficiency due to bimolecular recombination.

FIG. 6A shows a further embodiment of an optically-pumped laser in accordance with the present invention. In this embodiment, an additional layer 13 is provided between the substrate 11 and the organic active layer 12. The layer 13 has an index of refraction lower than that of the organic layer 12 and serves to increase optical confinement in the active layer in the direction normal to the surface of the device.

FIG. 6B shows yet another embodiment of an optically-pumped laser in accordance with the present invention. In this embodiment, the layer 13 is deposited on a ridge-patterned substrate. In this case, the layer 13 forms a ridge on top of the substrate 11 on which the active organic layer 12 is deposited. In this embodiment, the optical mode is confined in both the z-direction as well as in the y-direction. The width of the layers 12 and 13 should preferably be narrow enough to support only a single lateral optical-mode (e.g.,  $1\text{--}10 \mu\text{m}$ ). The thickness of the active organic layer 12 should be approximately equal to the reciprocal of the absorption coefficient of the host material at the wavelength of the light with which the device is pumped. If a reflective layer (not shown) is placed between the layer 13 and the substrate 11, the thickness of the organic layer 12 should be approximately half the reciprocal of the absorption coefficient of the host material at the wavelength of the light with which the device is pumped. To protect the laser device of FIG. 6B, the device can be overcoated with a transparent material (not shown) whose index of refraction is lower than that of the active organic layer 12.

In addition to the optically-pumped embodiments discussed above, the present invention also provides an electrically-pumped organic semiconductor laser.

FIG. 7A shows an embodiment of an electrically-pumped laser device in accordance with the present invention. A bottom electrode 31, a bottom cladding layer 32, an organic active layer 33, a top cladding layer 34 and a top electrode

**35** are deposited, in sequence, over a substrate **30**. The optical confinement in the active layer **33** depends on the indices of refraction of the cladding layers **32** and **34**.

As in the case of the optically-pumped laser device, the active layer **33** can be composed of Alq<sub>3</sub>/DCM. Either one of the cladding layers is composed of a hole conducting material, such as MgF<sub>2</sub> doped with TPD. To get good hole mobility, a 10% concentration of TPD will suffice. The other one of the cladding layers is composed of an electron conducting material, such as Alq<sub>3</sub> or MgF<sub>2</sub> doped with Alq<sub>3</sub>. For either cladding layer **32** or **34**, the MgF<sub>2</sub> can be replaced with another alkali halide such as LiF, KF or KI or with a transparent, low index of refraction, conducting organic material. Electrons and holes are injected into the active layer **33** where the energy is transferred from the conducting host material to the dopant molecules, which emit light.

An optical resonator is formed by the edges of the film, i.e., mirror facets **M1** and **M2**. At least one of the electrodes **31** and **35** is patterned into a stripe oriented in the, x-direction. That portion of the active material which is electrically pumped experiences a change in optical gain, thus forming a waveguide in the lateral direction (i.e., the gain-guiding effect).

In the electrically-pumped laser device of the present invention, the index of refraction of the active layer **33** must be higher than that of the cladding layers **32** and **34**. This ensures that most of the mode overlaps with the gain layer. Preferably, the indices of refraction of the cladding layers **32** and **34** should be substantially equal to provide optimal optical confinement.

The cladding layers **32** and **34** should be thick enough to substantially prevent absorption of the optical mode at the electrodes **31** and **35** and to allow for efficient current injection. The thicknesses of the cladding layers can be determined in a known manner. For single-mode operation, the thickness of the active layer **33** should be substantially equal to the lasing wavelength divided by twice the index of refraction of the active layer. For higher modes, the thickness of the active layer **33** should be accordingly greater.

Optical confinement can also be achieved by photo-bleaching the active layer **33** to define a waveguide in the active layer. Using this technique, once the active layer **33** has been deposited, a photomask is applied which partially covers the active layer **33** and the layer is exposed to intense UV light in an O<sub>2</sub> environment. The unmasked portions of the active layer **33** are thus bleached, lowering their index of refraction. The masked portion of the active layer **33** retains its original, higher index of refraction and is thus optically confined in a lateral direction.

Optical confinement can also be achieved by patterning the substrate or bottom cladding layer to achieve index guiding (similar to the optically-pumped embodiment of FIG. 6B). For example, photo-bleaching can be used on the bottom cladding layer **32** to create an index modulated distributed Bragg reflector under the active layer **33**.

An optical resonator can also be formed in the z-direction. In this case, the top and bottom electrodes also serve as optical mirrors, or, if the electrodes are transparent to light, high reflectivity mirrors can be added on both sides of the structure. The maximum of the optical mode of this structure should spatially match the position of the optical layer. Furthermore, the wavelength of the optical mode should overlap with the gain spectrum of the dopant molecule.

FIG. 7B shows a further embodiment of an electrically-pumped laser device in accordance with the present invention. In this embodiment, the bottom electrode **31** extends

beyond the laser structure so as to provide a contact surface. Additionally, an insulator **37** is provided on a side of the laser structure and a contact **36** extending from the upper electrode **35** to the surface of the substrate **30** is deposited on the insulator.

The present invention was developed with funding provided, in part, by the Air Force Office of Scientific Research and by the National Science Foundation.

The subject invention as disclosed herein may be used in conjunction with co-pending applications: "High Reliability, High Efficiency, Integratable Organic Light Emitting Devices and Methods of Producing Same," Ser. No. 08/774,119 (filed Dec. 23, 1996); "Novel Materials for Multicolor LED's," Ser. No. 08/850,264 (filed May 2, 1997); "Electron Transporting and Light Emitting Layers Based on Organic Free Radicals," Ser. No. 08/774,120 (filed Dec. 23, 1996); "Multicolor Display Devices," Ser. No. 08/772,333 (filed Dec. 23, 1996); "Red-Emitting Organic Light Emitting Devices (LED's)," Ser. No. 08/774,087 (filed Dec. 23, 1996); "Driving Circuit For Stacked Organic Light Emitting Devices," Ser. No. 08/792,050 (filed Feb. 3, 1997); "High Efficiency Organic Light Emitting Device Structures," Ser. No. 08/772,332 (filed Dec. 23, 1996); "Vacuum Deposited, Non-Polymeric Flexible Organic Light Emitting Devices," Ser. No. 08/789,319 (filed Jan. 23, 1997); "Displays Having Mesa Pixel Configuration," Ser. No. 08/794,595 (filed Feb. 3, 1997); "Stacked Organic Light Emitting Devices," Ser. No. 08/792,046 (filed Feb. 3, 1997); "High Contrast Transparent Organic Light Emitting Device Display," Ser. No. 08/821,380 (filed Mar. 20, 1997); "Organic Light Emitting Devices Containing A Metal Complex of 5-Hydroxy-Quinoxaline as A Host Material," Ser. No. 08/838,099 (filed Apr. 14, 1997), and "Light Emitting Devices Having High Brightness," Ser. No. 08/844,353 (filed Apr. 18, 1997), each co-pending application being incorporated herein by reference in its entirety. The subject invention may also be used in conjunction with the subject matter of each of co-pending U.S. patent application Ser. Nos. 08/354,674, 08/613,207, 08/632,322 and 08/693,359 and provisional patent application Ser. Nos. 60/010,013, 60/024,001 and 60/025501, each of which is also incorporated herein by reference in its entirety.

What is claimed is:

1. A laser comprising

a substrate; and

a layer of thin film organic material arranged on the substrate,

wherein the organic material has an index of refraction greater than an index of refraction of the substrate, and the organic material lases when pumped to thereby produce laser light;

wherein the layer of organic material includes two reflective facets substantially parallel to each other, thereby forming an optical resonator; and

wherein the organic material includes a host material doped with a guest material.

2. The laser of claim 1, wherein the organic material includes a photoluminescent organic material doped with a laser dye.

3. The laser of claim 2, wherein the photoluminescent organic material includes tris(8-hydroxyquinoline) aluminum.

4. The laser of claim 2, wherein the laser dye includes DCM.

5. The laser of claim 1, wherein the organic material is applied onto the substrate by vacuum deposition.

6. The laser of claim 1, wherein an electroluminescent spectrum of the host material and an absorption spectrum of the guest material overlap.

7. The laser of claim 1, wherein energy absorbed by the host material is transferred to the guest material.

8. The laser of claim 1, wherein the substrate includes glass.

9. The laser of claim 1, wherein the organic material comprises small molecules.

10. The laser of claim 1, wherein the laser is incorporated into a communications device.

11. The laser of claim 1, wherein the laser is incorporated into a printer.

12. The laser of claim 1, wherein the laser is incorporated into an etching system.

13. The laser of claim 1, wherein the laser is incorporated into a measurement device.

14. The laser of claim 1, wherein the laser is incorporated into an optical memory device.

15. A laser comprising

a substrate; and

a layer of thin film organic material arranged on the substrate,

wherein the organic material has an index of refraction greater than an index of refraction of the substrate, and the organic material lases when pumped to thereby produce laser light;

wherein the layer of organic material includes two reflective facets substantially parallel to each other, thereby forming an optical resonator; and

wherein the organic material includes a photoluminescent organic material doped with a laser dye.

16. The laser of claim 15, wherein the photoluminescent organic material includes tris(8-hydroxyquinoline) aluminum.

17. The laser of claim 15, wherein the laser dye includes DCM.

18. The laser of claim 15, wherein the organic material is applied onto the substrate by vacuum deposition.

19. The laser of claim 15, wherein an electroluminescent spectrum of the photoluminescent organic material and an absorption spectrum of the laser dye overlap.

20. The laser of claim 15, wherein energy absorbed by the photoluminescent organic material is transferred to the laser dye.

21. The laser of claim 15, wherein the substrate includes glass.

22. The laser of claim 15, wherein the organic material comprises small molecules.

23. The laser of claim 15, wherein the laser is incorporated into a communications device.

24. The laser of claim 15, wherein the laser is incorporated into a printer.

25. The laser of claim 15, wherein the laser is incorporated into an etching system.

26. The laser of claim 15, wherein the laser is incorporated into a measurement device.

27. The laser of claim 15, wherein the laser is incorporated into an optical memory device.

28. A laser comprising:

a substrate;

a first electrode arranged on the substrate;

a first cladding layer arranged on the first electrode;

an active organic layer arranged on the first cladding layer;

a second cladding layer arranged on the active organic layer; and

a second electrode arranged on the second cladding layer; wherein the active organic layer includes two reflective facets substantially parallel to each other, thereby forming an optical resonator; and

wherein the active organic layer includes a host material doped with a guest material.

29. The laser of claim 28, wherein the active organic layer includes a photoluminescent organic material doped with a laser dye.

30. The laser of claim 28, wherein the first cladding layer includes a hole conducting material and the second cladding layer includes an electron conducting material.

31. The laser of claim 28, wherein the first cladding layer includes an electron conducting material and the second cladding layer includes a hole conducting material.

32. The laser of claim 28, wherein the active organic layer has an index of refraction greater than an index of refraction of the first cladding layer and greater than an index of refraction of the second cladding layer.

33. The laser of claim 28, wherein the active organic layer includes a photoluminescent organic material doped with a laser dye.

34. The laser of claim 33, wherein the photoluminescent organic material includes tris(8-hydroxyquinoline) aluminum.

35. The laser of claim 33, wherein the laser dye includes DCM.

36. The laser of claim 28, wherein an electroluminescent spectrum of the host material and an absorption spectrum of the guest material overlap.

37. The laser of claim 28, wherein energy absorbed by the host material is transferred to the guest material.

38. The laser of claim 28, wherein the substrate includes glass.

39. The laser of claim 28, wherein the active organic layer comprises small molecules.

40. The laser of claim 28, wherein the laser is incorporated into a communications device.

41. The laser of claim 28, wherein the laser is incorporated into a printer.

42. The laser of claim 28, wherein the laser is incorporated into an etching system.

43. The laser of claim 28, wherein the laser is incorporated into a measurement device.

44. The laser of claim 28, wherein the laser is incorporated into an optical memory device.

45. A laser comprising:

a substrate;

a first electrode arranged on the substrate;

a first cladding layer arranged on the first electrode;

an active organic layer arranged on the first cladding layer;

a second cladding layer arranged on the active organic layer; and

a second electrode arranged on the second cladding layer; wherein the active organic layer includes two reflective facets substantially parallel to each other, thereby forming an optical resonator; and

wherein the active organic layer includes a photoluminescent organic material doped with a laser dye.

46. The laser of claim 45, wherein the first cladding layer includes a hole conducting material and the second cladding layer includes an electron conducting material.

47. The laser of claim 45, wherein the first cladding layer includes an electron conducting material and the second cladding layer includes a hole conducting material.

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48. The laser of claim 45, wherein the active organic layer has an index of refraction greater than an index of refraction of the first cladding layer and greater than an index of refraction of the second cladding layer.

49. The laser of claim 45, wherein the active organic layer includes a photoluminescent organic material doped with a laser dye.

50. The laser of claim 49, wherein the photoluminescent organic material includes tris(8-hydroxyquinoline) aluminum.

51. The laser of claim 45, wherein the laser dye includes DCM.

52. The laser of claim 45, wherein an electroluminescent spectrum of the host material and an absorption spectrum of the guest material overlap.

53. The laser of claim 45, wherein energy absorbed by the host material is transferred to the guest material.

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54. The laser of claim 45, wherein the substrate includes glass.

55. The laser of claim 45, wherein the active organic layer comprises small molecules.

56. The laser of claim 45, wherein the laser is incorporated into a communications device.

57. The laser of claim 45, wherein the laser is incorporated into a printer.

58. The laser of claim 45, wherein the laser is incorporated into an etching system.

59. The laser of claim 45, wherein the laser is incorporated into a measurement device.

60. The laser of claim 45, wherein the laser is incorporated into an optical memory device.

\* \* \* \* \*

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 6,396,860 B1  
DATED : May 28, 2002  
INVENTOR(S) : Kozlov et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 1,

Line 15, change "inthis" to -- in this --;

Line 23, change "in is" to -- in --;

Column 5,

Line 27, change "level:of" to -- level of --

Line 35, after "spectrograph.)" delete "FIG.4 shows the dependence of the device's" and in line 36, insert -- FIG. 4 shows the dependence of the device's -- before "peak";

Column 7,

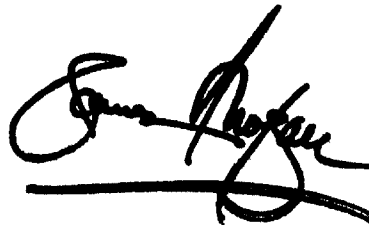
Line 19, after "the" delete ","; and

Column 11,

Line 11, change "claim 45," to -- claim 49, --.

Signed and Sealed this

First Day of April, 2003

A handwritten signature in black ink, appearing to read "James E. Rogan", written over a horizontal line.

JAMES E. ROGAN  
*Director of the United States Patent and Trademark Office*